

Protection IC for 1-Cell Battery Pack

Features

- High Detection Accuracy
 - Over-charge Detection: ±15mV
 - Over-discharge Detection: ±35mV
 - Discharge Over-current Detection: $\pm 10 mV/$ $\pm 15 mV$
 - Charge Over-current Detection: ±20mV
- High Withstand Voltage
 - Absolute maximum ratings: 28V (V- pin and CO pin)
- Ultra Small Package
 - SOT-23-5
 - SOT-23-6
 - DFN-1.6X1.6-6L
 - SON-1.6X1.6-6L

Application

- Mobile phone battery packs
- Digital camera battery packs
- Bluetooth earphone Li-ion battery module

Typical Application Circuit

Description

The NT1713 series are the 1-cell protection IC for lithium-ion/lithium-polymer rechargeable battery pack. The high accuracy voltage detector and delay time circuits are built in NT1713 series with state-of-art design and process.

To minimize power consumption, NT1713 series activates power down mode when an over-discharge event is detected (for power-down mode enabled version). Besides, NT1713 series performs protection functions with four external components for miniaturized PCB.

The tiny package is especially suitable for compact portable device, i.e. slim mobile phone and Bluetooth earphone.





Package and Pin Description



Pin No.	Symbol	Pin description
1	V-	Voltage detection between V- pin and Vss pin (Over-current / charger detection pin)
2	Vdd	Connection for positive power supply input
3	Vss	Connection for negative power supply input
4	DO	Connection of discharge control FET gate
5	CO	Connection of charge control FET gate

SOT-23-6 6 5 4 A A A 0

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Pin No.	Symbol	Pin description
1	DO	Connection of discharge control FET gate
r	Voltage detection between V- pin and	
Z	V-	(Over-current / charger detection pin)
3	CO	Connection of charge control FET gate
4	NC	No connection
5	Vdd	Connection for positive power supply input
6	Vss	Connection for negative power supply input

DFN-1.6X1.6-6L

1	 []	6
2		5
3		4

Pin No.	Symbol	Pin description
1	NC	No connection
2	CO	Connection of charge control FET gate
3	DO	Connection of discharge control FET gate
4	Vss	Connection for negative power supply input
5	Vdd	Connection for positive power supply input
6	V-	Voltage detection between V- pin and VSS pin (Over-current / charger detection pin)

SON-1.6X1.6-6L



Pin No.	Symbol	Pin description
1	NC	No connection
2	CO	Connection of charge control FET gate
3	DO	Connection of discharge control FET gate
4	Vss	Connection for negative power supply input
5	Vdd	Connection for positive power supply input
6	V-	Voltage detection between V- pin and VSS pin
		(Over-current / charger detection pin)



Block Diagram





Ordering Information



Product version code:

Table1: Detection threshold level table

Product Name	Version Code	Pack- age Type	Over- charge Detection Voltage	Over- charge Hysteresis Voltage	Over- discharge detection voltage	Over- discharge release voltage	Discharge over- current detection	Charge over- current detection	Load short- circuiting detection voltage	0V Battery Charge Function	Delay Time
			V _{DET1} (V)	V _{HYS1} (V)	V _{DET2} (V)	V _{REL2} (V)	V _{DET3} (V)	V _{DET4} (V)	V _{SHORT} (V)		Table 2
NT1713A	HFA	A6/B4/C1	4.280	0.00	2.3	2.3	0.10	-0.1	0.5	Un-avai lable	(1)
NT1713A	HFB	A6/B4/C1	4.280	0.00	2.3	2.3	0.13	-0.1	0.5	Un-avai lable	(1)
NT1713A	HQA	A5/A6/C1	4.280	0.15	2.8	3.1	0.15	-0.1	0.5	Un-avai lable	(2)
NT1713A	HQB	A5/A6/C1	4.280	0.15	2.8	3.1	0.10	-0.1	0.5	Un-avai lable	(2)
NT1713A	HQC	A6/B4/C1	4.280	0.00	2.8	3.1	0.15	-0.1	0.5	Un-avai lable	(1)
NT1713A	KKA	A5/A6/C1	4.325	0.20	2.5	2.9	0.15	-0.1	0.5	Un-avai lable	(2)
NT1713A	NHA	A5/A6/C1	4.425	0.20	2.4	2.4	0.10	-0.1	0.5	Un-avai lable	(1)
NT1713A	NHB	A5/A6/B4/C1	4.425	0.20	2.4	2.4	0.15	-0.1	0.5	Un-avai lable	(1)
NT1713A	NHC	A5/A6/B4/C1	4.425	0.20	2.4	2.4	0.20	-0.1	0.5	Un-avai lable	(1)
NT1713A	NQA	C1	4.425	0.20	2.8	3.0	0.038	-0.05	0.3	Availabl e	(1)

Table2: Delay Time table

Delay time	Over-charge delay	Over-discharge	Discharge	Charge	Load short-circuiting
	time	delay time	over-current delay	over-current delay	delay time
			time	time	
	t _{VDET1} (S)	t _{vDET2} (mS)	t _{vDET3} (mS)	t _{vDET4} (mS)	t _{short} (uS)
(1)	1.0 +/- 20%	125 +/- 20%	8.0 +/- 20%	8.0 +/- 20%	400 +/- 20%
(2)	1.2 +/- 20%	150 +/- 20%	9.0 +/- 20%	9.0 +/- 20%	300 +/- 20%

Remark Please contact our sales office for the products with detection voltage value other than those specified above.

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Marking Information



Product name vs. Version code

Due du et	Version Code	Version Code					
Name		(3)(4)(5) Version Code SOT-23-5	(3)(4)(5) Version Code SOT-23-6	(3)(4) Version Code DFN-1.6X1.6-6L	(3)(4) Version Code SON-1.6X1.6-6L		
NT1713A	HFA	-	HFA	10	10		
NT1713A	HFB	-	HFB	11	11		
NT1713A	HQA	HQA	HQA	-	13		
NT1713A	HQB	HQB	HQB	-	14		
NT1713A	HQC	-	HQC	12	12		
NT1713A	KKA	ККА	ККА		18		
NT1713A	NHA	NHA	NHA	-	15		
NT1713A	NHB	NHB	NHB	16	16		
NT1713A	NHC	NHC	NHC	17	17		
NT1713A	NQA	-	-	-	19		

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Absolute Maximum Ratings

Symbol	Descriptions		Rating	Units
V_{DD}	Supply	Voltage	-0.3 to 7	V
V-	V- pin		V_{DD} - 28 to V_{DD} + 0.3	V
V _{co}	Quite ut Valta da	CO pin	V_{DD} -28 to V_{DD} + 0.3	V
V _{DO}	Output voitage	DO pin	Vss - 0.3 to V _{DD} + 0.3	V
T _{OPT}	Operating Temperature Range		-40 to +85	°C
T _{STG}	Storage Temp	erature Range	-55 to +125	°C

Applying any over "Absolute Maximum Ratings" practice can permanently damage the device. These data are indicated the absolute maximum values only but not implied any operating performance.

Flectrical Characteristics (For Li-ion)

Electr	rical Characteristics (F	or Li-ion)			(Ta	= 25°C)
Symbol	Item	Conditions	MIN	ТҮР	MAX	Unit
Detectio	on Voltage	•		•		•
V_{DET1}	Over-charge detection voltage		V _{DET1} -0.015	V_{DET1}	V _{DET1} +0.015	V
$V_{\rm HYS1}$	Over-charge hysteresis voltage		V _{HYS1} -0.020	$V_{\rm HYS1}$	V _{HYS1} +0.020	V
V_{DET2}	Over-discharge detection voltage		V _{DET2} -0.035	V_{DET2}	V _{DET2} +0.035	V
M	Over-discharge release voltage	$V_{DET2} \neq V_{REL2}$	V _{REL2} -0.050	V _{REL2}	V _{REL2} +0.050	V
V _{REL2}		$V_{DET2} = V_{REL2}$	V _{REL2} -0.035	V_{REL2}	V _{REL2} +0.035	V
	Discharge over-current detection	V _{DD} =3.5V	V _{DET3} -0.010	V _{DET3}	V _{DET3} +0.010	V
V		$V_{DET3}(typ) {\leq} 0.150V$				v
V DET3	voltage	$V_{DD}=3.5V$	V 0.015	V _{DET3}	V _{DET3} +0.015	V
		V _{DET3} (typ)>0.150V	V _{DET3} -0.015			v
V_{DET4}	Charge over-current detection	$V_{DD}=3.5V$	V _{DET4} -0.020	V_{DET4}	V _{DET4} +0.020	V
		V _{DD} =3.5V	V 0.10	V	V 10.10	V
	Load short-circuiting detection	V _{SHORT} (typ)=0.50V	V _{SHORT} -0.10	V _{SHORT}	V _{SHORT} +0.10	v
V SHORT	voltage	V _{DD} =3.5V				V
		V _{SHORT} (typ)=0.30V	V _{SHORT} -0.05	V SHORT	v _{SHORT} +0.05	v



(Continued)

Symbol	Item	Conditions	MIN	ТҮР	MAX	Unit
Detectio	on Delay Time 【Table 2 Delay	time (1)]				
t _{VDET1}	Output delay time of over-charge	-	0.8	1.0	1.2	S
t _{VDET2}	Output delay time of over-discharge	-	100	125	150	ms
t _{vDET3}	Output delay time of discharge over current	$V_{DD}=3.5V$	6.4	8.0	9.6	ms
t _{vDET4}	Output delay time of charge over current	$V_{DD}=3.5V$	6.4	8.0	9.6	ms
t _{short}	Output delay time of Load short-circuiting detection	$V_{DD}=3.5V$	320	400	480	us
Detectio	on Delay Time 【Table 2 Delay	time (2)]				
t _{VDET1}	Output delay time of over-charge	-	0.96	1.2	1.44	S
t _{VDET2}	Output delay time of over-discharge	-	120	150	180	ms
t _{vDET3}	Output delay time of discharge over current	$V_{DD}=3.5V$	7.2	9.0	10.8	ms
t _{vDET4}	Output delay time of charge over current	V_{DD} =3.5V	7.2	9.0	10.8	ms
t _{short}	Output delay time of Load short-circuiting detection	V_{DD} =3.5V	240	300	360	us
Current	Consumption (power-down fu	inction enabled)				
V_{DD}	Operating input voltage	V_{DD} - V_{SS}	2.0		6.0	V
I _{DD}	Supply current	V _{DD} =3.5V, V-=0V	1.0	3.0	5.5	uA
I _{STANDBY}	Power-down current (power-down function enabled IC only)	V_{DD} =1.8V, V- floating			0.1	uA
0V batte	ery Charging Function					
V _{0CHA}	0 V battery charge starting charger voltage	0 V battery charging function "available"	0.5	1.0	1.5	V
V _{OINH}	0V battery charge inhibition battery voltage	0 V battery charging function "unavailable" (Vcharger=4V~14V)	0.5	1.0	1.5	v
Output	Resistance					
R _{COH}	CO pin H resistance	V _{CO} =3.0V, V _{DD} =3.5V, V-=0V	1.25	2.50	5.00	KΩ
R _{COL}	CO pin L resistance	V _{CO} =0.5V, V _{DD} =4.5V, V-=0V	0.75	1.50	3.00	KΩ
R _{DOH}	DO pin H resistance	V _{DO} =3.0V, V _{DD} =3.5V, V-=0V	1.25	2.50	5.00	KΩ
R _{DOL}	DO pin L resistance	V _{DO} =0.5V, V _{DD} =1.8V, V-=0V	1.75	3.50	7.00	KΩ
V- inter	nal Resistance					
R _{VMD}	Internal resistance between V- and V_{DD}	V _{DD} =1.8V, V-=0V	100	300	900	KΩ
R _{VMS}	Internal resistance between V- and V _{ss}	V _{DD} =3.5V, V-=1.0V	50	100	300	ΚΩ

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Electrical Characteristics (For Li-ion)

Electrical Characteristics (For Li-ion) (Ta = -10 ~ 60							
Symbo	l Item	Conditions	MIN	ТҮР	MAX	Unit	
Detecti	on Voltage						
V_{DET1}	Over-charge detection voltage		V _{DET1} -0.025	V_{DET1}	V _{DET1} +0.025	V	
$V_{\rm HYS1}$	Over-charge hysteresis voltage		V _{HYS1} -0.030	V _{HYS1}	V _{HYS1} +0.030	V	
V_{DET2}	Over-discharge detection voltage		V _{DET2} -0.050	V_{DET2}	V _{DET2} +0.050	V	
		$V_{DET2} \neq V_{REL2}$	V _{REL2} -0.080	V _{REL2}	V _{REL2} +0.080	V	
V _{REL2}	Over-discharge release voltage	$V_{DET2} = V_{REL2}$	V _{REL2} -0.050	V _{REL2}	V _{REL2} +0.050	V	
	Discharge over-current detection	V _{DD} =3.5V V _{DET3} (typ)≦0.150V	V _{DET3} -0.015	V _{DET3}	V _{DET3} +0.015	v	
V _{DET3}	voltage	V _{DD} =3.5V V _{DET3} (typ)>0.150V	V _{DET3} -0.020	V _{DET3}	V _{DET3} +0.020	v	
V_{DET4}	Charge over-current detection	V _{DD} =3.5V	V _{DET4} -0.030	V_{DET4}	V _{DET4} +0.030	V	
V	Load short-circuiting detection voltage	V _{DD} =3.5V V _{SHORT} (typ)=0.50V	V _{SHORT} -0.15	V _{SHORT}	V _{SHORT} +0.15	v	
V SHORT		V _{DD} =3.5V V _{SHORT} (typ)=0.30V	V _{SHORT} -0.09	V _{SHORT}	V _{SHORT} +0.09	v	
Detecti	on Delay Time 【Table 2 Delay	time (1)]				-	
t _{VDET1}	Output delay time of over-charge	-	0.7	1.0	1.3	s	
t _{VDET2}	Output delay time of over-discharge	-	88	125	163	ms	
t _{vDET3}	Output delay time of discharge over current	V _{DD} =3.5V	5.0	8.0	11.0	ms	
t _{vDET4}	Output delay time of charge over current	V _{DD} =3.5V	5.0	8.0	11.0	ms	
t _{short}	Output delay time of Load short-circuiting detection	V_{DD} =3.5V	280	400	520	us	
Detecti	on Delay Time 【Table 2 Delay	time (2)]	-		-		
t_{VDET1}	Output delay time of over-charge	-	0.84	1.2	1.56	s	
t_{VDET2}	Output delay time of over-discharge	-	105	150	195	ms	
t _{vDET3}	Output delay time of discharge over current	V _{DD} =3.5V	6.0	9.0	12.0	ms	
t _{vDET4}	Output delay time of charge over current	V _{DD} =3.5V	6.0	9.0	12.0	ms	
t _{short}	Output delay time of Load short-circuiting detection	$V_{DD}=3.5V$	210	300	390	us	



(Continued)

Current Consumption (power-down function enabled)									
V _{DD}	Operating input voltage	$V_{DD} - V_{SS}$	2.0		6.0	V			
I_{DD}	Supply current	V _{DD} =3.5V, V-=0V	1.0	3.0	6.0	uA			
I _{STANDBY}	Power-down current (power-down function enabled IC only)	V_{DD} =1.8V, V- floating			0.1	uA			
0V batt	0V battery Charging Function								
V _{0CHA}	0 V battery charge starting charger voltage	0 V battery charging function "available"	0.3	1.0	1.7	V			
V _{OINH}	0V battery charge inhibition battery voltage	0 V battery charging function "unavailable" (Vcharger=4V~14V)	0.3	1.0	1.7	v			
Output	Output Resistance								
R _{COH}	CO pin H resistance	V _{CO} =3.0V, V _{DD} =3.5V, V-=0V	1.00	2.50	5.00	KΩ			
R _{COL}	CO pin L resistance	V _{CO} =0.5V, V _{DD} =4.5V, V-=0V	0.60	1.50	3.00	KΩ			
R _{DOH}	DO pin H resistance	V _{DO} =3.0V, V _{DD} =3.5V, V-=0V	1.00	2.50	5.00	KΩ			
R _{DOL}	DO pin L resistance	V _{DO} =0.5V, V _{DD} =1.8V, V-=0V	1.40	3.50	7.00	KΩ			
V- internal Resistance									
R _{VMD}	Internal resistance between V- and V_{DD}	V _{DD} =1.8V, V-=0V	78	300	900	KΩ			
R _{VMS}	Internal resistance between V- and V_{SS}	V _{DD} =3.5V, V-=1.0V	26	100	300	KΩ			

*: The specification for this temperature range is guaranteed by design because products are not screened at high to low temperature.



Test Circuits

• Over-charge, over-discharge and the release detection voltages (test circuit 1)

- 1) Set V1=3.5V, V2=0V, S1=ON and S2=OFF, then NT1713 series enters operating mode.
- 2) Increase V1 voltage (from 3.5V) gradually. The V1 voltage is the over-charge detection voltage (V_{DET1}) when CO pin goes to low (from high).
- Decrease V1 gradually. The voltage gap is the over-charge hysteresis detection voltage (V_{HYS1}) when CO pin goes to high (from low) again.
- Continue decreasing V1. The V1 voltage is the over-discharge detection voltage (V_{DET2}) when DO pin goes to low (from high). Then increase V1 gradually. The V1 voltage is the over-discharge release detection voltage (V_{REL2}), when DO pin goes to high (from low).

Note: The over-charge and over-discharge release voltages are defined in versions.

■ Discharge over-current detection voltage (test circuit 1)

- 1) Set V1=3.5V, V2=0V, S1=ON and S2=OFF and NT1713 series enters operating condition.
- Increase V2 (from 0V) gradually. The V2 voltage is the discharge over-current detection voltage (V_{DET3}) when DO pin goes to low (from high).

■ Charge over-current detection voltage (test circuit 1)

- 1) Set V1=3.5V, V3=0V, S1=OFF and S2=ON and NT1713 series enters operating condition.
- Increase V3 gradually. The V3 voltage is the charge over-current detection voltage (V_{DET4}) when CO pin goes to low (from high).

■ Load short-circuiting detection voltage (test circuit 1)

- 1) Set V1=3.5V, V2=0V, S1=ON and S2=OFF and NT1713 series enters operating condition.
- 2) Increase V2 immediately (within 10uS) till DO pin goes to low (from high) with a delay time which is between the minimum and the maximum of Load short-circuiting delay time.

• Over-charge, over-discharge delay time (test circuit 1)

- 1) Set V1=3.5V, V2=0V, S1=ON and S2=OFF to enter operating condition.
- 2) Increase V1 from V_{DET1} -0.2V to V_{DET1} +0.2V immediately (within 10us). The over-charge detection delay time (t_{VDET1}) is the period from the time V1 gets to V_{DET1} +0.2V till CO pin goes to low (from high).
- 3) Set V1=3.5V, V2=0V, S1=ON and S2 = OFF to enter operating condition.
- 4) Decrease V1 from V_{DET2} +0.2V to V_{DET2} -0.2V immediately (within 10us). The over-discharge detection delay time (t_{VDET2}) is the period from the time V1 gets to V_{DET2} -0.2V till DO pin goes to low (from high).

Discharge over-current delay time (test circuit 1)

- 1) Set V1=3.5V, V2=0V, S1=ON and S2=OFF to enter operating condition.
- Increase V2 from 0V to 0.25V immediately (within 10us). The discharge over-current detection delay time (tVDET3) is the period from the time V2 gets to 0.25V till DO pin goes to low (from high).

• Charge over-current delay time (test circuit 1)

- 1) Set V1=3.5V, V3=0V, S1=OFF and S2=ON to enter operating condition.
- 2) Increase V3 from 0V to 0.3V immediately (within 10us). The charge over-current detection delay time (t_{VDET4}) is the period from the time V3 gets to 0.3V till CO pin goes to low (from high).

• Load short-circuiting delay time (test circuit 1)

- 1) Set V1=3.5V, V2=0V, S1=ON and S2=OFF to enter operating condition.
- 2) Increase V2 from 0V to 1.0V immediately (within 10us). The Load short-circuiting detection voltage delay time (t_{SHORT}) is the period from the time V2 gets to 1.0V till DO pin goes to low (from high).

• Operating & power down current consumption (test circuit 2)

- 1) Set V1=3.5V, V2=0V and S1=ON to enter operating condition and measure the current I1. I1 is the operating condition current consumption (I_{DD}).
- 2) Set V1=V2=1.8V and S1=ON enter over-discharge condition and measure current I1. I1 is the power down current consumption (I_{STANDBY}). (for power-down mode enabled version)



■ Resistance between V- and VDD, V- and Vss (test circuit 2)

- 1) Set V1=1.8V, V2=0V and S1=ON and NT1713 series enters over-discharge condition. V1/I2 is the internal resistance between V- and VDD pin (R_{VMD}).
- 2) Set V1=3.5V, V2=1.0V and S1=ON and NT1713 series enters discharge over-current condition. V2/I2 is the internal resistance between V- and Vss pin (R_{VMS}).

• **Output resistance** (test circuit 3)

- 1) Set V1=3.5V, V2=0V, V3=3.0V, S1=OFF and S2=ON to enter operating condition. (V3-V1)/I2 is the internal resistance (R_{COH}).
- 2) Set V1=4.5V, V2=0V, V3 =0.5V, S1=OFF and S2=ON to enter over-charge condition. V3/I2 is the internal resistance (R_{COL}).
- 3) Set V1=3.5V, V2=0V, V3=3.0V, S1=ON and S2=OFF to enter operating condition. (V3-V1)/I2 is the internal resistance (R_{DOH}).
- 4) Set V1=1.8V, V2=0V, V3 =0.5V, S1=ON and S2=OFF to enter over-discharge condition. V3/I2 is the internal resistance (R_{DOL}).
- OV battery charge starting charger voltage (products with OV battery charging function is "Available") (test circuit 4)
 - 1) Set V1=V2=0V, decrease V2 gradually.
 - 2) The V2 voltage is the 0V charge starting voltage (V_{0CHA}) when CO pin voltage goes to (V2+0.1) from V2.
- OV battery charge inhibition battery voltage (products with OV battery charging function is "Unavailable") (test circuit 4)
 - 1) Set V1=1.6V, V2=-4V then decrease V1 gradually.
 - 2) The V1 voltage is the 0V charge inhibition voltage (V_{0INH}) when CO pin voltage goes to V2 from V1 **Note:** The charger voltage should not be higher than 14V.
- Shorten mode for overcharge and over-discharge functions by force voltage to DO pin (test circuit 5)
 - 1) Set V1=3.5V then NT1713 series enters operating mode.
 - 2) Set V2= 0.5V, increase V1 voltage (from 3.5V) gradually. The V1 voltage is the over-charge detection voltage (V_{DET1}) when CO pin goes to low (from high).
 - Decrease V1 gradually. The voltage gap is the over-charge hysteresis detection voltage (V_{HYS1}) when CO pin goes to high (from low).
 - 4) Continue decreasing V1. The V1 voltage is the over-discharge detection voltage (V_{DET2}) when the voltage drop (V_{R1K}*I1) on DO pin by shorten mode circuit. Then increase V1 gradually. The V1 voltage is the over-discharge release detection voltage (V_{RL2}), when DO pin goes to high (from low).

Recommended:

- 1) "0 V charge available" doesn't means NT1713 series can recover the zero-V cell to be full charged if this cell has been already damaged due to too low voltage.
- 2) For safety consideration, we strongly recommended to select "0 V charge inhibition" version to prevent from charging a damaged cell.



Test Circuit



Test circuit 5

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Operation

The NT1713 series provides over-charge, over-discharge, discharge over-current, charge over-current and load short-circuiting protections for the 1-cell battery pack. NT1713 series continuously monitors the voltage of battery between VDD pin and VSS pin to control over-charge and over-discharge protections. When the battery pack is in charging stage, the current flows from the charger to the battery through EB+ and EB-; the voltage between V-pin and VSS pin is negative. On the other hand, when the battery pack is in discharging stage, the current flows from battery to the load through EB+ and EB-; the voltage between V-pin and VSS pin is positive. The NT1713 series also monitors the voltage which is determined by the current of charge and discharge and the series Rds(on) of MOSFETs between V-pin and VSS pin to detect charge over-current and discharge over-current current conditions.

(1) Normal Condition (Operation mode)

The NT1713 series turns both the charging and discharging control MOSFETs on when the voltage of battery is in the range from over-charge detection voltage (V_{DET1}) to over-discharge detection voltage (V_{DET2}), and the V- pin voltage is in the range from over-current detection voltage (V_{DET4}) to discharge over-current detection voltage (V_{DET4}). This is called the normal condition that charging and discharging can be carried out freely.

Caution: The NT1713 series may be needed connecting a charger to return to normal condition, when the battery is connected for the first time.

(2) Over-charge Condition

1) Over-charge Protection:

When the VDD voltage is higher than the over-charge detection voltage (V_{DET1}) and lasts for longer than the over-charge detection delay time (t_{VDET1}), NT1713 series turns off the external charging MOSFET to protect the pack from being over-charged, which CO pin goes to "L" from "H" level.

2) Over-charge Protection Release:

When the battery voltage is lower than $V_{DET1} - V_{HYS1}$ and the V- pin voltage is between charge over-current detection voltage (V_{DET4}) and discharge over-current detection voltage (V_{DET3}), the NT1713 series would be automatically released from this condition.

When the battery voltage is lower than V_{DET1} and charger is removed, the NT1713 series can be automatically released from this condition.

(3) Over-discharge Condition

1) Over-discharge Protection:

When the VDD voltage is lower than the over-discharge detection voltage (V_{DET2}) and lasts longer than over-discharge detection delay time (t_{VDET2}), NT1713 series turns off the external discharge MOSFET to protect the pack from being over-discharged, which DO pin goes to "L" from "H" level. In over-discharge condition V- pin is pulled-up to VDD by a resistor (RVMD) between the V- pin and VDD pin. After that, when V- pin voltage is higher than VDD/2(Typ), the IC gets to power down mode.

2) Over-discharge Protection Release:

The over-discharge protection is automatically released when

- (a) a charger is connected and V- pin voltage is lower than -0.7V (Typ.) and battery voltage is higher than the over-discharge voltage(V_{DET2}), or
- (b) a charger is connected, and V- pin voltage is higher than -0.7V (Typ.) and battery voltage is higher than the over-discharge release voltage(V_{REL2}).



(4) Discharge Over-current Condition

- 1) Discharge Over-current Protection:
 - (a) Discharge over-current protection occurs when V- pin voltage is between V_{DET3} and V_{SHORT} and lasts for a certain delay time (t_{VDET3}).
 - (b) Load short-circuiting protection occurs when V- pin voltage is higher than V_{SHORT} and lasts for a certain delay time (t_{SHORT}).

When above conditions happen, the DO pin goes to "L" from "H" to turn off the discharging MOSFET. In discharge over-current and load short-circuiting conditions, V- pin is pulled-down to Vss pin by the internal resistor (Rvms).

2) Discharge Over-current and Load Short-Circuiting Protection Release:

The IC detects the status by monitoring V- pin voltage that is inversely proportional to the impedance (Rload) between two terminals (EB+ and EB-). The Rload increases while the V- pin voltage decreases. When the V- pin voltage equals to V_{SHORT} or lower, discharge over-current status returns to normal mode and the circuit will be automatic recovery.

The relation between V- and Rload is shown as follows:

$$V\text{-=} \ \frac{\text{RVMS}}{\text{RVMS} + \text{Rload}} \ \text{X VDD} \ ; \ \text{ when V-} \ \leq \ \text{Vshort}$$

(5) Charge Over-current Condition

1) Charge Over-current Protection:

When the voltage of V- pin is lower than charge over-current detection voltage (V_{DET4}) and lasts for a certain delay time (t_{DET4}) or longer, the CO pin goes to "L" from "H" to turn off the charging MOSFET.

2) Charge Over-current Release:

Charge over-current protection can be automatically released by disconnecting the charger.

(6) Power Down Condition

1) Entering to Power Down Mode:

NT1713 series enters the power down mode when over-discharge protection occurs and V- pin voltage is higher than VDD/2 (typical). The V- pin voltage is pulled-up to the VDD through the R_{VMD} resistor. The internal circuits is shut off, therefore, the power-down current ($I_{STANDBY}$) is reduced to be low 0.1uA (Max.).

2) Power Down Mode Release:

The power down mode is automatically released when a charger is connected and V- pin voltage is lower than VDD/2 (typical).

Note: Power down condition is for power down mode enabled version only.



Timing Chart





- (d) Normal condition
- (e) Overcharge condition
- (f) Charge over-current condition
- *: The charger is assumed to charge with a constant current.





(2) Over-discharge, Discharge Over-current, Load Short-Circuiting Operation

- (e) Normal condition
- (f) Over-discharge condition
- (g) Discharge over-current condition
- (h) Load short-circuit condition
- *: The charger is assumed to charge with a constant current.



Recommended Application Circuit



Symbol	Parts	Purpose	Recommended	Min.	Max.	Remarks	
FET1	N channel MOSFET	Discharge control	-	-	-	*1) Gate to source withstand voltage \geq Charger voltage.	
FET2	N channel MOSFET	Charge control	-	-	-		
R1	Resistor	ESD protection, for power fluctuation	470Ω	100Ω	1ΚΩ	*2) Set Resistance to the value 2R1 <u><</u> R2.	
C1	Capacitor	For power fluctuation	0.1uF	0.022uF	1.0uF	*3) Install a 0.022uF capacitor or higher.	
R2	Resistor	Protection for reverse connection of a charger	1ΚΩ	300Ω	10ΚΩ	*4) The resistor is preventing big current when a charger is connected in reverse.	
C2	Capacitor	For ESD protection	0.1uF	-	-	*5) Protected MOSFET after system ESD	
C3	Capacitor	For ESD protection	0.1uF	-	-		
C4	Capacitor	For ESD protection	0.1uF	-	-	*5) Reduce noise of load and improve system ESD performance.	
C5	Capacitor	For ESD protection	0.1uF	-	-		



*1) If the threshold voltage of FET is lower than 0.4V, the FET may failed to stop the charging current. If the FET has a threshold voltage equal to or higher than the over-discharge detection voltage, discharging may be stopped before over-discharge is detected.

If the charger voltage is higher than the withstanding voltage between the gate and source, the FET may be damaged.

*2) Employing an over-specification (listed in above table) R1 may result in over-charge detection voltage and release voltage higher than the defined voltage the IC may be damaged caused by over absolute maximum rating of VDD voltage when a

If R1 has a higher resistance, the IC may be damaged caused by over absolute maximum rating of VDD voltage when a charger is connected reversely.

- *3) Applying a smaller capacitance C1 to system, DO may failed to function when load short-circuiting is detected.
- *4) R1 and R2 resistors are current limit resistance for a charger connected reversibly or a large voltage charger that exceeds the absolute rating for VCC is connected, when we connect reverse charger the current flows from charger to R2, internal ESD diode and R1. This current will increase R1 voltage drop. Which can exceed VCC(max). In this case better to use smaller value for R1 and bigger value for R2. But small value of R1 will reduce R-C filter performance and system ESD reliability. Too big value of R2 can cause over-current automatic release problem.
- If R2 resistance is higher than $2k\Omega$, the charging current may not be cut when a high-voltage charger is connected.
- *5) As followed this recommended table, the system ESD level could be reached at least ±12KV. We can improve system ESD by connect C2 ~ C5 capacitor of 0.1uF. Both C2 and C3 are protected MOSFET from being assaulted by system ESD. C4 and C5 are improved system ESD and reduce imported noise by load.

Caution: 1) The above constants may be changed without notice. 2) The application circuit above is for reference only. To determine the correct constants, evaluation of actual application is required.

Precautions: 1) The application condition for the input voltage, output voltage, and load current should not exceed the package power dissipation. 2) Do not apply an electrostatic discharge to this IC that exceeds the performance ratings

of the built-in electrostatic protection circuit.



PCB Schematic



Layout Reference (takes DFN-1.6x1.6-6L for example)

Top layer



Note: To leave thermal pad floating is suggested (shown above). It can connect to VSS/VDD level as well.



PCB symbol list:

Symbol	Parts	Symbol	Parts
B+	Positive terminal of Battery	P+	Positive terminal of charger or load
B-	negative terminal of Battery	P-	negative terminal of charger or load

BOM list:

Standard application circuit:

Symbol	Parts	Footprint	Value	Remarks
U1	NT1713 Series	DFN-1.6x1.6-6L	-	-
U2	N-MOSFET	TSSOP8	AO8810	Cut off charge or discharge current
R1	Resistor	0402 @ 1/16W	470Ω	Low pass filter with C1 and ESD protection
R2	Resistor	0402 @ 1/16W	1KΩ	ESD protection
C1	Capacitor	0402 @ 1/16W	0.1uF	Low pass filter with R1 and ESD protection



Package Information

SOT-23-5 Dimensions







PCB Land Pattern



SYMBOL	MIN	NOM	MAX
Α	-	-	1.45
A1	0.00	—	0.15
A2	0.90	1.15	1.30
b	0.30	0.4	0.50
C	0.08	—	0.22
D	2.70	2.90	3.10
Е	2.60	2.80	3.00
E1	1.40	1.60	1.80
е		0.95 BSC	_
e1	_	1.90 BSC	_
L	0.30	0.45	0.60
L1	1 – 0.6 REF		_
L2	L2 - 0.25		_
0 0°		4 °	8°
θ1	5°	10°	15°

NOTES: 1. All dimensions show in mm 2. Reference: JEDECMO-178AA 3. SOT23-5 / SOT23-6

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SOT-23-6 Dimensions







PCB Land Pattern



SYMBOL	MIN	NOM	ΜΔΧ
O IMBOL	INITY		
A		—	1.45
A1	0.00	-	0.15
A2	0.90	1.15	1.30
b	0.30	0.4	0.50
c	0.08	—	0.22
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e		0.95 BSC	
e1	-	1.90 BSC	
L	L 0.30		0.60
L1	L1 –		_
L2	L2 –		_
θ	0°	4°	8°
θ 1	5°	10°	15°

NOTES: 1. All dimensions show in mm 2. Reference: JEDECMO-178AA 3. SOT23-5 / SOT23-6



DFN-1.6X1.6-6L Dimension



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SON-1.6x1.6-6L Dimension

Note: All dimensions show in mm



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